

Title (en)
FIELD-EFFECT-TRANSISTOR INFRARED SENSOR HAVING A MOVABLE GATE ELECTRODE

Title (de)
FELDEFFEKTTRANSISTOR-INFRAROTSENSOR MIT BEWEGLICHER GATEELEKTRODE

Title (fr)
CAPTEUR INFRAROUGE À TRANSISTOR À EFFET DE CHAMPS MUNI D'ÉLECTRODE GRILLE

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Application
EP 14728142 A 20140527

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Abstract (en)
[origin: WO2014195185A1] The invention relates to an infrared sensor (100) designed as a field-effect transistor, comprising a semiconductor substrate (117), which has a drain connection (110) and a source connection, wherein the drain connection (110) is separated from the source connection (115) by a channel region (105). The sensor (100) also comprises a gate unit (125), which can be moved in relation to the channel region (105) and which is arranged above the channel region, wherein the gate unit (125) is designed to change the shape of the gate unit and/or the distance (d) of at least one part (140) of the gate unit (125) from the channel region (105) in response to received electromagnetic radiation (135).

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